W Walukiewicz

List of Publications by Citations

254 papers	16,543 citations	62 h-index	124 g-index
257 ext. papers	17,599 ext. citations	3.4 avg, IF	6.1 L-index

#	Paper	IF	Citations
254	Band Anticrossing in GaInNAs Alloys. *Physical Review Letters*, **1999**, 82, 1221-1224	7.4	1359
253	Unusual properties of the fundamental band gap of InN. *Applied Physics Letters*, **2002**, 80, 3967-3969	3.4	1254
252	Superior radiation resistance of In1−xGaxN alloys: Full-solar-spectrum photovoltaic material system. *Journal of Applied Physics*, **2003**, 94, 6477-6482	2.5	503
251	Small band gap bowing in In1−xGaxN alloys. *Applied Physics Letters*, **2002**, 80, 4741-4743	3.4	498
250	Effect of the location of Mn sites in ferromagnetic Ga1−xMnxAs on its Curie temperature. *Physical Review B*, **2002**, 65,	3.3	461
249	Electron mobility in modulation-doped heterostructures. *Physical Review B*, **1984**, 30, 4571-4582	3.3	402
248	Effects of the narrow band gap on the properties of InN. *Physical Review B*, **2002**, 66,	3.3	346
247	Temperature dependence of the fundamental band gap of InN. *Journal of Applied Physics*, **2003**, 94, 4457-4460	2.5	337
246	Valence-band anticrossing in mismatched III-V semiconductor alloys. *Physical Review B*, **2007**, 75,	3.3	310
245	Intrinsic limitations to the doping of wide-gap semiconductors. *Physica B: Condensed Matter*, **2001**, 302-303, 123-134	2.8	279
244	Origin of the 0.82-eV electron trap in GaAs and its annihilation by shallow donors. *Applied Physics Letters*, **1982**, 40, 342-344	3.4	264
243	Band anticrossing in highly mismatched III□V semiconductor alloys. *Semiconductor Science and Technology*, **2002**, 17, 860-869	1.8	262
242	Amphoteric native defects in semiconductors. *Applied Physics Letters*, **1989**, 54, 2094-2096	3.4	242
241	Electron mobility and free-carrier absorption in InP; determination of the compensation ratio. *Journal of Applied Physics*, **1980**, 51, 2659	2.5	242
240	Electron mobility and free-carrier absorption in GaAs: Determination of the compensation ratio. *Journal of Applied Physics*, **1979**, 50, 899-908	2.5	229
239	Engineering the electronic band structure for multiband solar cells. *Physical Review Letters*, **2011**, 106, 028701	7.4	225
238	Diluted II-VI oxide semiconductors with multiple band gaps. *Physical Review Letters*, **2003**, 91, 246403	7.4	219

237	Native point defects in low-temperature-grown GaAs. *Applied Physics Letters*, **1995**, 67, 279-281	3.4	217
236	Large, nitrogen-induced increase of the electron effective mass in InyGa1−yNxAs1−x. *Applied Physics Letters*, **2000**, 76, 2409-2411	3.4	212
235	Structure and electronic properties of InN and In-rich group III-nitride alloys. *Journal Physics D: Applied Physics*, **2006**, 39, R83-R99	3	211
234	Nature of the fundamental band gap in GaNxP1−x alloys. *Applied Physics Letters*, **2000**, 76, 3251-3253	3.4	211
233	Effects of electron concentration on the optical absorption edge of InN. *Applied Physics Letters*, **2004**, 84, 2805-2807	3.4	210
232	Electron mobility in AlxGa1−xN/GaN heterostructures. *Physical Review B*, **1997**, 56, 1520-1528	3.3	185
231	Evidence for p-type doping of InN. *Physical Review Letters*, **2006**, 96, 125505	7.4	176
230	Fermi-level stabilization energy in group III nitrides. *Physical Review B*, **2005**, 71,	3.3	172
229	Interaction of localized electronic states with the conduction band: band anticrossing in II-VI semiconductor ternaries. *Physical Review Letters*, **2000**, 85, 1552-5	7.4	162
228	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. *Nature Materials*, **2012**, 11, 444-9	27	148
227	Band-edge hydrostatic deformation potentials in III-V semiconductors. *Physical Review Letters*, **1987**, 59, 501-504	7.4	148
226	Finite element simulations of compositionally graded InGaN solar cells. *Solar Energy Materials and Solar Cells*, **2010**, 94, 478-483	6.4	145
225	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. *Journal of Crystal Growth*, **2004**, 269, 119-127	1.6	145
224	Metastability of Oxygen Donors in AlGaN. *Physical Review Letters*, **1998**, 80, 4008-4011	7.4	138
223	Band gaps of InN and group III nitride alloys. *Superlattices and Microstructures*, **2003**, 34, 63-75	2.8	137
222	Mechanism of Fermi-level stabilization in semiconductors. *Physical Review B*, **1988**, 37, 4760-4763	3.3	135
221	Persistent photoconductivity in n-type GaN. *Applied Physics Letters*, **1997**, 71, 1098-1100	3.4	133
220	Effect of nitrogen on the band structure of GaInNAs alloys. *Journal of Applied Physics*, **1999**, 86, 2349-2351	2.5	130

219	Optical properties of InxGa1−xN alloys grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **1998**, 84, 4452-4458	2.5	127
218	Modeling of InGaN/Si tandem solar cells. *Journal of Applied Physics*, **2008**, 104, 024507	2.5	126
217	Effect of polarization fields on transport properties in AlGaN/GaN heterostructures. *Journal of Applied Physics*, **2001**, 89, 1783	2.5	119
216	Multiband GaNAsP quaternary alloys. *Applied Physics Letters*, **2006**, 88, 092110	3.4	112
215	Band Anticrossing in III−N−V Alloys. *Physica Status Solidi (B): Basic Research*, **2001**, 223, 75-85	1.3	107
214	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. *Applied Physics Letters*, **2000**, 77, 3021-3023	3.4	105
213	Dependence of the fundamental band gap of AlxGa1−xN on alloy composition and pressure. *Journal of Applied Physics*, **1999**, 85, 8505-8507	2.5	100
212	Annealing studies of low-temperature-grown GaAs:Be. *Journal of Applied Physics*, **1992**, 71, 1699-1707	2.5	98
211	On the crystalline structure, stoichiometry and band gap of InN thin films. *Applied Physics Letters*, **2005**, 86, 071910	3.4	97
210	Mechanism of Schottky barrier formation: The role of amphoteric native defects. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1987**, 5, 1062		96
209	Universal bandgap bowing in group-III nitride alloys. *Solid State Communications*, **2003**, 127, 411-414	1.6	92
208	Large disparity between gallium and antimony self-diffusion in gallium antimonide. *Nature*, **2000**, 408, 69-72	50.4	90
207	Reduction of band-gap energy in GaNAs and AlGaNAs synthesized by N+ implantation. *Applied Physics Letters*, **1999**, 75, 1410-1412	3.4	90
206	Effect of nitrogen on the electronic band structure of group III-N-V alloys. *Physical Review B*, **2000**, 62, 4211-4214	3.3	89
205	Fermi level dependent native defect formation: Consequences for metal–semiconductor and semiconductor–semiconductor interfaces. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1988**, 6, 1257		85
204	Curie temperature limit in ferromagnetic Ga1−xMnxAs. *Physical Review B*, **2003**, 68,	3.3	83
203	Minority-carrier mobility in p-type GaAs. *Journal of Applied Physics*, **1979**, 50, 5040-5042	2.5	83
202	Pressure-dependent photoluminescence study of ZnO nanowires. *Applied Physics Letters*, **2005**, 86, 153113	3.4	80

201	Effect of band anticrossing on the optical transitions in GaAs1−xNx/GaAs multiple quantum wells. *Physical Review B*, **2001**, 64,	3.3	80
200	Electron mobility in n-type GaAs at 77 K: Determination of the compensation ratio. *Journal of Applied Physics*, **1982**, 53, 769-770	2.5	80
199	Valence band hybridization in N-rich GaN1−xAsx alloys. *Physical Review B*, **2004**, 70,	3.3	76
198	Carrier localization of as-grown n-type gallium nitride under large hydrostatic pressure. *Physical Review B*, **1996**, 53, 1322-1326	3.3	71
197	Effect of oxygen on the electronic band structure in ZnOxSe1−x alloys. *Applied Physics Letters*, **2003** , 83, 299-301	3.4	70
196	Enhancement of Curie temperature in Ga1−xMnxAs/Ga1−yAlyAs ferromagnetic heterostructures by Be modulation doping. *Applied Physics Letters*, **2003**, 83, 4220-4222	3.4	67
195	Hydrostatic pressure dependence of the fundamental bandgap of InN and In-rich group III nitride alloys. *Applied Physics Letters*, **2003**, 83, 4963-4965	3.4	63
194	Hole transport and photoluminescence in Mg-doped InN. *Journal of Applied Physics*, **2010**, 107, 113712	2.5	62
193	Band gap bowing parameter of In1−xAlxN. *Journal of Applied Physics*, **2008**, 104, 123501	2.5	62
192	Band anticrossing in GaP1−xNx alloys. *Physical Review B*, **2002**, 65,	3.3	62
191	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. *Physical Review B*, **2003**, 67,	3.3	61
190	Band structure of highly mismatched semiconductor alloys: Coherent potential approximation. *Physical Review B*, **2002**, 65,	3.3	61
189	Electronic Band Structure of GaNxPyAs1−x−y Highly Mismatched Alloys: Suitability for Intermediate-Band Solar Cells. *Physical Review Applied*, **2014**, 1,	4.3	60
188	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. *Physical Review B*, **2000**, 61, R13337-R13340	3.3	60
187	Band anticrossing in highly mismatched SnxGe1−x semiconducting alloys. *Physical Review B*, **2008**, 77,	3.3	59
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185	Band structure and optical properties of InyGa1−yAs1−xNx alloys. *Physical Review B*, **2001**, 65,	3.3	58
184	Carrier scattering by native defects in heavily doped semiconductors. *Physical Review B*, **1990**, 41, 10218-10220	3.3	58

183	Effects of surface states on electrical characteristics of InN and In1−xGaxN. *Physical Review B*, **2007**, 76,	3.3	57
182	Current status of research and development of III-N-V semiconductor alloys. *Semiconductor Science and Technology*, **2002**, 17, 741-745	1.8	57
181	Phosphorus antisite defects in low-temperature InP. *Physical Review B*, **1993**, 47, 4111-4114	3.3	57
180	Effect of Nitrogen-Induced Modification of the Conduction Band Structure on Electron Transport in GaAsN Alloys. *Physica Status Solidi (B): Basic Research*, **1999**, 216, 135-139	1.3	56
179	Synthesis and optical properties of II-O-VI highly mismatched alloys. *Journal of Applied Physics*, **2004** , 95, 6232-6238	2.5	55
178	Fermi level stabilization energy in cadmium oxide. *Journal of Applied Physics*, **2010**, 107, 113706	2.5	54
177	Highly mismatched crystalline and amorphous GaN1−xAsx alloys in the whole composition range. *Journal of Applied Physics*, **2009**, 106, 103709	2.5	54
176	Mg-doped InN and InGaN - Photoluminescence, capacitance-voltage and thermopower measurements. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 873-877	1.3	53
175	Crystal structure and properties of CdxZn1−xO alloys across the full composition range. *Applied Physics Letters*, **2013**, 102, 232103	3.4	52
174	High quality InN/GaN heterostructures grown by migration enhanced metalorganic chemical vapor deposition. *Applied Physics Letters*, **2004**, 84, 1892-1894	3.4	52
173	Mutual passivation of electrically active and isovalent impurities. *Nature Materials*, **2002**, 1, 185-9	27	51
172	Effects of piezoelectric field on defect formation, charge transfer, and electron transport at GaN/AlxGa1−xN interfaces. *Applied Physics Letters*, **1998**, 73, 339-341	3.4	51
171	Electron mobility in InN and III-N alloys. *Journal of Applied Physics*, **2007**, 102, 073705	2.5	46
170	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaN heterostructures. *Applied Physics Letters*, **2002**, 80, 1228-1230	3.4	46
169	Arsenic antisite-related defects in low-temperature MBE grown GaAs. *Semiconductor Science and Technology*, **1992**, 7, 1037-1041	1.8	45
168	Determination of free hole concentration in ferromagnetic Ga1−xMnxAs using electrochemical capacitance-voltage profiling. *Applied Physics Letters*, **2002**, 81, 844-846	3.4	44
167	Electronic structure of Ga1−xMnxAs analyzed according to hole-concentration-dependent measurements. *Physical Review B*, **2010**, 81,	3.3	43
166	Synthesis of GaNxAs1− thin films by pulsed laser melting and rapid thermal annealing of N+-implanted GaAs. *Journal of Applied Physics*, **2003**, 94, 1043-1049	2.5	43

165	Mg doped InN and confirmation of free holes in InN. *Applied Physics Letters*, **2011**, 98, 042104	3.4	41
164	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. *Physical Review B*, **2008**, 78,	3.3	41
163	Compensating point defects in He+4-irradiated InN. *Physical Review B*, **2007**, 75,	3.3	41
162	Synthesis of InNxP1 thin films by N ion implantation. *Applied Physics Letters*, **2001**, 78, 1077-1079	3.4	39
161	Formation of diluted III V nitride thin films by N ion implantation. *Journal of Applied Physics*, **2001**, 90, 2227-2234	2.5	37
160	Growth and characterization of ZnO1 Sx highly mismatched alloys over the entire composition. *Journal of Applied Physics*, **2015**, 118, 215702	2.5	36
159	Full multiple scattering analysis of XANES at the Cd L3 and O K edges in CdO films combined with a soft-x-ray emission investigation. *Physical Review B*, **2010**, 82,	3.3	36
158	Effects of point defects on thermal and thermoelectric properties of InN. *Applied Physics Letters*, **2011**, 98, 012108	3.4	36
157	Theoretical transport studies of p-type GaN/AlGaN modulation-doped heterostructures. *Applied Physics Letters*, **1999**, 74, 2405-2407	3.4	36
156	Band-gap bowing effects in BxGa1 As alloys. *Journal of Applied Physics*, **2003**, 93, 2696-2699	2.5	35
155	Transport-to-quantum lifetime ratios in AlGaN/GaN heterostructures. *Applied Physics Letters*, **2002**, 80, 2508-2510	3.4	34
154	Pressure dependence of Schottky barrier height at the Pt/GaAs interface. *Applied Physics Letters*, **1988**, 53, 974-976	3.4	34
153	Shallow donor associated with the main electron trap (EL2) in melt-grown GaAs. *Applied Physics Letters*, **1983**, 43, 112-114	3.4	34
152	Lattice location of diffused Zn atoms in GaAs and InP single crystals. *Journal of Applied Physics*, **1991**, 69, 2998-3006	2.5	33
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150	Metal-insulator transition by isovalent anion substitution in Ga1-xMnxAs: implications to ferromagnetism. *Physical Review Letters*, **2008**, 101, 087203	7.4	32
149	Annealing of AsGa-related defects in LT-GaAs: The role of gallium vacancies. *Journal of Electronic Materials*, **1993**, 22, 1401-1404	1.9	32
148	GaN1 Bix: Extremely mismatched semiconductor alloys. *Applied Physics Letters*, **2010**, 97, 141919	3.4	31

147	Temperature dependence of the band gap of ZnSe1−xOx. *Applied Physics Letters*, **2009**, 95, 151907	3.4	31
146	Band anticrossing in group II-OxVI1−x highly mismatched alloys: Cd1−yMnyOxTe1−x quaternaries synthesized by O ion implantation. *Applied Physics Letters*, **2002**, 80, 1571-1573	3.4	30
145	Formation of a DX center in InP under hydrostatic pressure. *Physical Review Letters*, **1992**, 68, 3619-3622	7.4	30
144	Response to "Comment on 'Electron mobility in modulation-doped heterostructures' ". *Physical Review B*, **1985**, 32, 2645-2646	3.3	30
143	Probing and modulating surface electron accumulation in InN by the electrolyte gated Hall effect. *Applied Physics Letters*, **2008**, 93, 262105	3.4	29
142	High electron mobility InN. *Applied Physics Letters*, **2007**, 90, 162103	3.4	29
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140	Effect of film thickness on the incorporation of Mn interstitials in Ga1−xMnxAs. *Applied Physics Letters*, **2005**, 86, 042102	3.4	27
139	Enhanced nitrogen incorporation by pulsed laser annealing of GaNxAs1−x formed by N ion implantation. *Applied Physics Letters*, **2002**, 80, 3958-3960	3.4	27
138	Nitrogen-induced enhancement of the free electron concentration in sulfur implanted GaNxAs1−x. *Applied Physics Letters*, **2000**, 77, 2858-2860	3.4	27
137	Band anticrossing in dilute nitrides. *Journal of Physics Condensed Matter*, **2004**, 16, S3355-S3372	1.8	26
136	Electronic effects determining the formation of ferromagnetic III1−xMnxV alloys during epitaxial growth. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 25, 171-180	3	25
135	Effects of rapid quenching on the impurity site location in Zn-diffused InP. *Journal of Applied Physics*, **1993**, 74, 86-90	2.5	25
134	Electronic band structure of ZnO-rich highly mismatched ZnO1−xTex alloys. *Applied Physics Letters*, **2015**, 106, 092101	3.4	24
133	Highly mismatched N-rich GaN1−xSbx films grown by low temperature molecular beam epitaxy. *Applied Physics Letters*, **2013**, 102, 102104	3.4	24
132	Native-defect-controlled n-type conductivity in InN. *Physica B: Condensed Matter*, **2006**, 376-377, 436-439	2.8	24
131	Acoustic-phonon scattering in modulation-doped heterostructures. *Physical Review B*, **1988**, 37, 8530-8533	3.3	24
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128	Electronic structure of CdO studied by soft X-ray spectroscopy. *Journal of Electron Spectroscopy and Related Phenomena*, **2011**, 184, 249-253	1.7	22
127	Diluted ZnMnTe oxide: a multi-band semiconductor for high efficiency solar cells. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 660-663	1.3	22
126	p-type InN and In-rich InGaN. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 1820-1824	1.3	21
125	Multiphonon resonance Raman scattering in InxGa1−xN. *Physical Review B*, **2005**, 72,	3.3	21
124	Strain-engineered ferromagnetic In1−xMnxAs films with in-plane easy axis. *Applied Physics Letters*, **2005**, 86, 112512	3.4	20
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122	Deep-level defects in silicon and the band-edge hydrostatic deformation potentials. *Physical Review B*, **1987**, 36, 9392-9394	3.3	20
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120	Properties of Ga1−xMnxAs with high x (>0.1). *Journal of Applied Physics*, **2008**, 103, 07D136	2.5	19
119	Growth and characterization of highly mismatched GaN1−xSbx alloys. *Journal of Applied Physics*, **2014**, 116, 123704	2.5	18
118	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. *Applied Physics Letters*, **2012**, 101, 082109	3.4	18
117	Effect of native defects on optical properties of InxGa1−xN alloys. *Applied Physics Letters*, **2005**, 87, 161905	3.4	18
116	Optimum nitride concentration in multiband III-N-V alloys for high efficiency ideal solar cells. *Applied Physics Letters*, **2008**, 93, 174109	3.4	17
115	Activation of shallow dopants in II-VI compounds. *Journal of Crystal Growth*, **1996**, 159, 244-247	1.6	17
114	Application of The Amphoteric Native Defect Model to Diffusion and Activation of Shallow Impurities in III-V Semiconductors. *Materials Research Society Symposia Proceedings*, **1993**, 300, 421		17
113	Temperature dependence of photoluminescence from InNAsSb layers: The role of localized and free carrier emission in determination of temperature dependence of energy gap. *Applied Physics Letters*, **2013**, 102, 122109	3.4	16
112	Low gap amorphous GaN1−xAsx alloys grown on glass substrate. *Applied Physics Letters*, **2010**, 97, 101906	3.4	16

111	Determining surface Fermi level pinning position of InN nanowires using electrolyte gating. *Applied Physics Letters*, **2009**, 95, 173114	3.4	16
110	Effects of donor doping on Ga1−xMnxAs. *Applied Physics Letters*, **2008**, 93, 262505	3.4	16
109	Low-temperature grown compositionally graded InGaN films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1866-1869		16
108	Direct evidence of the Fermi-energy-dependent formation of Mn interstitials in modulation-doped Ga1−yAlyAs/Ga1−xMnxAs/Ga1−yAlyAs heterostructures. *Applied Physics Letters*, **2004**, 84, 4325-4327	3.4	16
107	Composition dependence of the hydrostatic pressure coefficients of the bandgap of ZnSe1−xTex alloys. *Physical Review B*, **2003**, 68,	3.3	16
106	Mutual passivation of group IV donors and nitrogen in diluted GaNxAs1−x alloys. *Applied Physics Letters*, **2003**, 83, 2844-2846	3.4	16
105	Doping-induced suppression of dislocation formation in semiconductors. *Physical Review B*, **1989**, 39, 8776-8779	3.3	16
104	Hole-scattering mechanisms in modulation-doped heterostructures. *Journal of Applied Physics*, **1986**, 59, 3577-3579	2.5	16
103	Determination of carrier concentration and compensation microprofiles in GaAs. *Journal of Applied Physics*, **1980**, 51, 2301	2.5	16
102	Magnetic-Field-Induced Energy Gap in HgTe Observed in Transport Measurements. *Physica Status Solidi (B): Basic Research*, **1975**, 71, 117-124	1.3	16
101	Electron mobility and thermoelectric power in pure mercury telluride. *Journal of Physics C: Solid State Physics*, **1976**, 9, 1945-1954		16
100	Temperature evolution of carrier dynamics in GaNxPyAs1−x−yalloys. *Journal of Applied Physics*, **2015**, 117, 175702	2.5	15
99	Surface Recombination in Semiconductors. *Materials Science Forum*, **1995**, 196-201, 1389-1394	0.4	15
98	Electronic properties of low-temperature InP. *Journal of Electronic Materials*, **1993**, 22, 1487-1490	1.9	15
97	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. *Semiconductor Science and Technology*, **2015**, 30, 085018	1.8	14
96	Surface photovoltage and modulation spectroscopy of E0and E+ transitions in GaNAs layers. *Thin Solid Films*, **2014**, 567, 101-104	2.2	14
95	Temperature dependence of E0 and E0 + SO transitions in In0.53Ga0.47BixAs1−x alloys studied by photoreflectance. *Journal of Applied Physics*, **2012**, 112, 113508	2.5	14
94	Mutual passivation effects in Si-doped diluted InyGa1−yAs1−xNx alloys. *Physical Review B*, **2003**, 68,	3.3	14

93	Defect Reactions at Metal-Semiconductor and Semiconductor-Semiconductor Interfaces. *Materials Research Society Symposia Proceedings*, **1989**, 148, 137		14
92	Highly mismatched GaN1−xSbxalloys: synthesis, structure and electronic properties. *Semiconductor Science and Technology*, **2016**, 31, 083001	1.8	13
91	High quality InxGa1−xN thin films with x > 0.2 grown on silicon. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1747-1749	1.3	13
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89	Size effect in parabolic GaAs/AlxGa1-xAs quantum wells. *Physical Review B*, **1991**, 44, 10909-10912	3.3	13
88	Dependence of transition-metal impurity levels on host composition in III-V semiconductors. *Physical Review B*, **1989**, 39, 10114-10119	3.3	13
87	Critical criterion for axial models of defects in as-grown n-type GaAs. *Physical Review B*, **1987**, 36, 9374-9377	3.3	13
86	Modeling of the atomic structure and electronic properties of amorphous GaN1−xAsx. *Computational Materials Science*, **2014**, 82, 100-106	3.2	12
85	Photoluminescence of energetic particle-irradiated InxGa1−xN alloys. *Applied Physics Letters*, **2006**, 88, 151101	3.4	12
84	Dopants and defects in InN and InGaN alloys. *Journal of Crystal Growth*, **2006**, 288, 278-282	1.6	12
83	Influence of microstructure on electrical properties of diluted GaNxAs1−x formed by nitrogen implantation. *Applied Physics Letters*, **2001**, 79, 931-933	3.4	12
82	Increased electrical activation in the near-surface region of sulfur and nitrogen coimplanted GaAs. *Applied Physics Letters*, **2000**, 77, 3607-3609	3.4	12
81	Near-band-edge photoluminescence emission in AlxGa1−xN under high pressure. *Applied Physics Letters*, **1998**, 72, 2274-2276	3.4	12
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79	Multicolor emission from intermediate band semiconductor ZnOSe. *Scientific Reports*, **2017**, 7, 44214	4.9	11
78	Nitrogen-related intermediate band in P-rich GaNPAs alloys. *Scientific Reports*, **2017**, 7, 15703	4.9	11
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75	Electrical and electrothermal transport in InN: The roles of defects. *Physica B: Condensed Matter*, **2009**, 404, 4862-4865	2.8	10
74	Effects of pressure on the band structure of highly mismatched Zn1−yMnyOxTe1−x alloys. *Applied Physics Letters*, **2004**, 84, 924-926	3.4	10
73	Effects of the d-donor level of vanadium on the properties of Zn1−xVxO films. *Applied Physics Letters*, **2015**, 106, 182101	3.4	9
72	Composition and optical properties of dilute-Sb GaN1−xSbxhighly mismatched alloys grown by MBE. *Journal Physics D: Applied Physics*, **2014**, 47, 465102	3	9
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70	Native defects in InxGa1−xN alloys. *Physica B: Condensed Matter*, **2006**, 376-377, 432-435	2.8	8
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67	Evidence of extreme type-III band offset at buried n-type CdO/p-type SnTe interfaces. *Physical Review B*, **2015**, 91,	3.3	7
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